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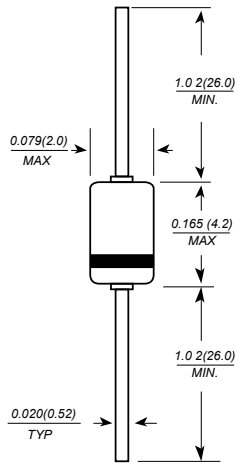
SILICON EPITAXIAL PLANAR DIODE

DO-35(GLASS)



Dimensions in millimeters

Features

- Low capacitance. (C = 3.0pF max)
- Short reverse recovery time. (t_{rr} = 8.0ns max)
- High reliability with glass seal.

Mechanical Data

- Case: DO-35, glass case
- Polarity: Color band denotes cathode
- Weight: 0.004 ounces, 0.13 grams

RoHS COMPLIANT

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	35	V
Reverse voltage	V_R	30	V
Peak forward current	I_{FM}	450	mA
Non-Repetitive peak forward surge current	I_{FSM}*	1	A
Average forward current	I_O	150	mA
Power dissipation	Pd	250	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	–65 to +175	°C

Note: Within 1s forward surge current.

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	0.64	—	0.80	V	I_F = 10mA
Reverse current	I_R	—	—	0.1	μA	V_R = 30V
Capacitance	C	—	—	3.0	pF	V_R = 1V, f = 1MHz
Reverse recovery time	t_{rr}*	—	—	8.0	ns	I_F = I_R = 10mA, Irr = 1mA

Note: Reverse recovery time test circuit

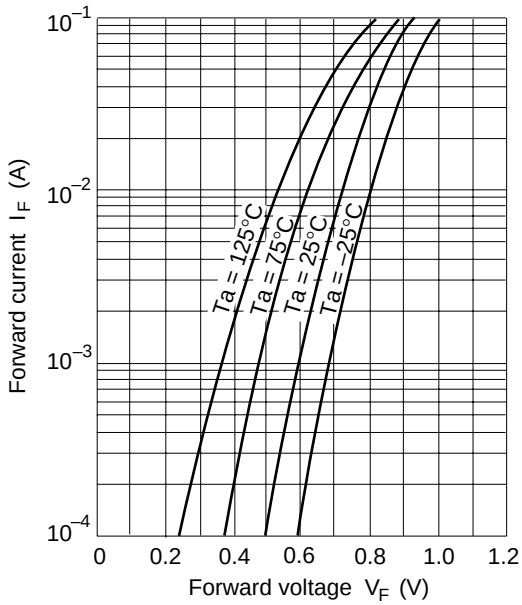


Fig.1 Forward current Vs. Forward voltage

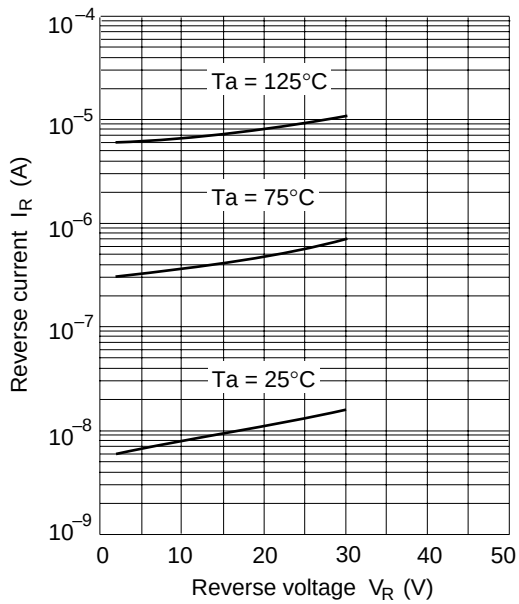


Fig.2 Reverse current Vs. Reverse voltage

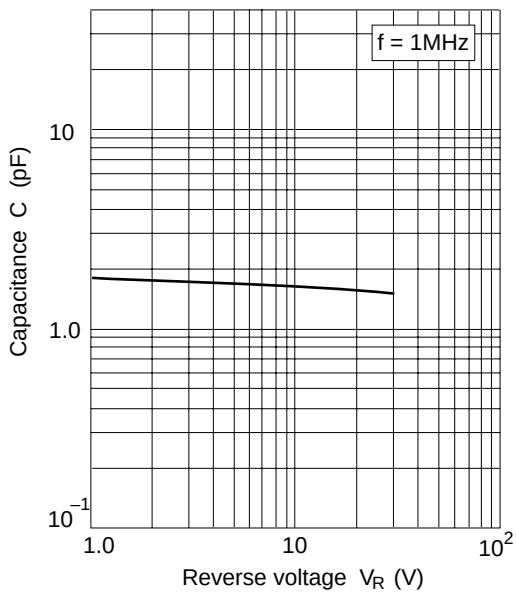


Fig.3 Capacitance Vs. Reverse voltage